Docket No.

240428US2S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Toru TANZAWA

SERIAL NO: NEW APPLICATION

GAU:

FILED:

HEREWITH

EXAMINER:

FOR:

NONVOLATILE SEMICONDUCTOR MEMORY CAPABLE OF GENERATING READ-MODE REFERENCE

CURRENT AND VERIFY-MODE REFERENCE CURRENT FROM THE SAME REFERENCE CELL

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

Marvin J. Spivak

Registration No. 24,913

C. Irvin McClelland Registration Number 21,124

22850

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

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LIST OF RELATED CASES

Docket Number	Serial or <u>Patent Number</u>	Filing or <u>Issue Date</u>	Inventor/ Applicant
PER CLIENT	09/953,227	09/17/01	TANZAWA et al.
217128US2	10/006,395	12/10/01	TAKANO et al.

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		OTHER RE	FERENCES (I	Including Author, Title, Date, Pertinent	t Pages, et	ic.)			
	AW	M. BAUER, et al. "A M Conference, Digest of	ULTILEVEL-CE Technical Pape	ELL 32MB FLASH MEMORY," 1995 IEE ers, February 1995, pgs. 132-133.	E Internation	onal Solid-	State Ci	ircuits	
	AX	G. CAMPARDO, et al. "A 40MM ² 3V 50MHZ 64MB 4-LEVEL CELL NOR-TYPE FLASH MEMORY," 2000 IEEE International Solid-State Circuits Conference, Digest of Technical Papers, February 2000, pgs. 274-275.							
	AY	D. ELMHURST, et al. "A 1.8V 128MB 125 MHZ MULTI-LEVEL CELL FLASH MEMORY WITH FLEXIBLE READ WHILE WRITE," ISSCC 2003 Digest of Technical Papers, February 2003, pgs. 286-287.							
	AZ				Additional References sheet(s) attached				
Examiner				Date Considered					
*Examiner: Ini	tial if re	eference is considered, t considered. Include co	whether or not py of this form	citation is in conformance with MPEP 60 with next communication to applicant.)9; Draw lin	e through	citation	if not in	